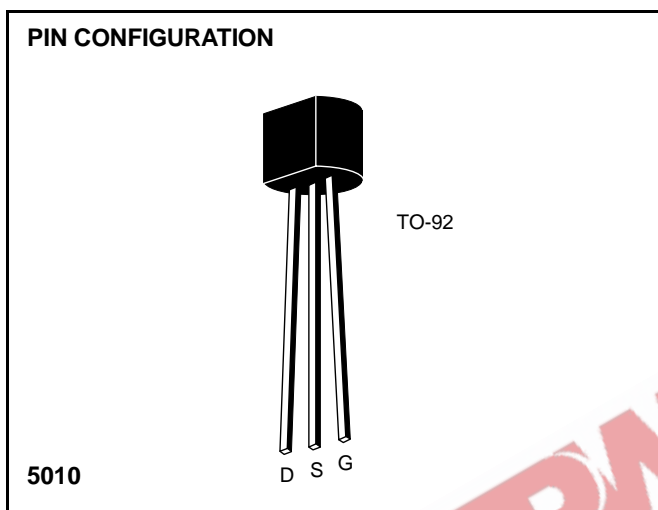


N-Channel JFET

General Purpose Amplifier/Switch



2N5457 – 2N5459



ABSOLUTE MAXIMUM RATINGS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

| | |
|-------------------------------------|---|
| Drain-Gate Voltage | 25V |
| Drain-Source Voltage | 25V |
| Continuous Forward Gate Current | 10mA |
| Storage Temperature Range | -65°C to $+150^\circ\text{C}$ |
| Operating Temperature Range | -55°C to $+135^\circ\text{C}$ |
| Lead Temperature (Soldering, 10sec) | $+300^\circ\text{C}$ |
| Power Dissipation | 310mW |
| Derate above 25°C | 2.82mW/ $^\circ\text{C}$ |

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

| Part | Package | Temperature Range |
|------------|--------------------------|---|
| 2N5457-59 | Plastic TO-92 | -55°C to $+135^\circ\text{C}$ |
| X2N5457-59 | Sorted Chips in Carriers | -55°C to $+135^\circ\text{C}$ |

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

| SYMBOL | PARAMETER | MIN | MAX | UNITS | TEST CONDITIONS |
|---------------|--|-------------|------|---------------|--|
| BV_{GSS} | Gate-Source Breakdown Voltage | -25 | | V | $I_G = -10\mu\text{A}$, $V_{DS} = 0$ |
| I_{GSS} | Gate Reverse Current | | -1.0 | nA | $V_{GS} = -15\text{V}$, $V_{DS} = 0$ |
| | | | -200 | | $V_{GS} = -15\text{V}$, $V_{DS} = 0$, $T_A = 100^\circ\text{C}$ |
| $V_{GS(off)}$ | Gate-Source Cutoff Voltage | 2N5457 -0.5 | -6.0 | V | $V_{DS} = 15\text{V}$, $I_D = 10\text{nA}$ |
| | | 2N5458 -1.0 | -7.0 | | |
| | | 2N5459 -2.0 | -8.0 | | |
| V_{GS} | Gate-Source Voltage | 2N5457 2.5 | | V | $V_{DS} = 15\text{V}$, $I_D = 100\mu\text{A}$, Typical |
| | | 2N5458 3.5 | | | $V_{DS} = 15\text{V}$, $I_D = 200\mu\text{A}$, Typical |
| | | 2N5459 4.5 | | | $V_{DS} = 15\text{V}$, $I_D = 400\mu\text{A}$, Typical |
| I_{DSS} | Zero-Gate-Voltage Drain Current (Note 1) | 2N5457 1.0 | 5.0 | mA | $V_{DS} = 15\text{V}$, $V_{GS} = 0$ |
| | | 2N5458 2.0 | 9.0 | | |
| | | 2N5459 4.0 | 16 | | |
| $ y_{fs} $ | Forward Transfer Admittance | 2N5457 1000 | 5000 | μS | $V_{DS} = 15\text{V}$, $V_{GS} = 0$, $f = 1\text{kHz}$ |
| | | 2N5458 1500 | 5500 | | |
| | | 2N5459 2000 | 6000 | | |
| $ y_{os} $ | Output Admittance | | 50 | μS | $V_{DS} = 15\text{V}$, $V_{GS} = 0$, $f = 1\text{kHz}$ |
| C_{iss} | Input Capacitance (Note 2) | | 7.0 | pF | $V_{DS} = 15\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$ |
| C_{rss} | Reverse Transfer Capacitance (Note 2) | | 3.0 | pF | $V_{DS} = 15\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$ |
| NF | Noise Figure (Note 2) | | 3.0 | dB | $V_{DS} = 15\text{V}$, $V_{GS} = 0$, $R_G = 1\text{MHz}$, $BW = 1\text{Hz}$, $f = 1\text{kHz}$ |

NOTES: 1. Pulse test required. $PW \leq 630\text{ms}$, duty cycle $\leq 10\%$.
2. For design reference only, not 100% tested.